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Amendment

(under Article 11 of the Japanese Patent Law)

To the Examiner of the Patent Office

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1. International Application No.

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4. Items to be amended

Claims

25 5. Contents of Amendments

(1) The last sentence of claim 1 "also functions as a drain electrode of the thin film transistor." is amended to "also functions as a drain electrode of the thin film transistor, a source electrode of the thin film transistor is

formed so as to be opposed to the pixel electrode in a thickness direction with the active layer interposed therebetween, and the pixel electrode has an area larger than that of the source electrode so as to cover the active layer on the source electrode substantially entirely.” This amendment
5 involves the incorporation of claim 2 before the amendment into claim 1.
(2) Claim 2 is cancelled.

6. List of attached documents

New sheet for page 11 (corresponding to pages 14 and 14/1 of the
10 English translation) of the claims 1 set